

NPN SILICON RF MICROWAVE TRANSISTOR

DESCRIPTION:

The **ASI SD1485-1** is Designed for Television Band III Applications up to 230 MHz.

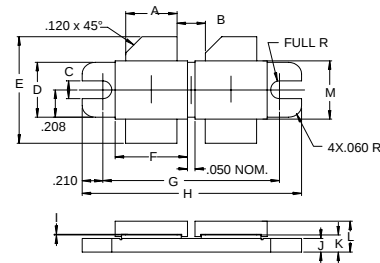
FEATURES:

- Common Emitter
- $P_G = 11$ dB at 100 W/225 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	25 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	3.0 V
P_{DISS}	385 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	0.45°C/W

PACKAGE STYLE .450 BAL FLG (B)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.373 / 9.47	.385 / 9.78
B	.205 / 5.21	
C	.120 / 3.25	.130 / 3.30
D	.411 / 10.44	.421 / 10.69
E	.825 / 20.96	.865 / 21.97
F	.525 / 13.34	.535 / 13.59
G	1.255 / 31.88	1.265 / 32.18
H	1.675 / 42.55	1.685 / 42.80
I	.002 / 0.05	.006 / 0.15
J	.095 / 2.41	.105 / 2.67
K	.115 / 2.92	.135 / 3.43
L		.250 / 6.35
M	.445 / 11.30	.457 / 11.61

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 100$ mA	65			V
BV_{CER}	$I_C = 100$ mA $R_{BE} = 15 \Omega$	60			V
BV_{CEO}	$I_C = 100$ mA	35			V
BV_{EBO}	$I_E = 20$ mA	3.0			V
I_{CES}	$V_{CB} = 32$ V			10	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 4.0$ A	20		70	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz	---	130	---	pF
P_G	$V_{CE} = 32$ V $I_C = 2 \times 500$ mA $f = 230$ MHz	11			dB
η_C	$P_{OUT} = 200$ W	50			%